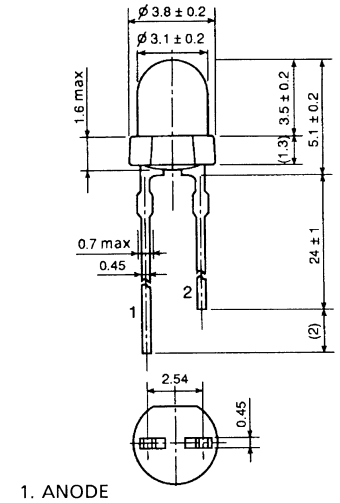
TOSHIBA InGaAℓP LED

TLRE62T(F),TLRME62T(F),TLSE62T(F),TLOE62T(F),TLYE62T(F), TLPYE62T(F),TLGE62T(F),TLFGE62T(F),TLPGE62T(F)

Panel Circuit Indicators

- Lead(Pb)-free products (lead: Sn-Ag-Cu)
- φ3 mm package
- InGaAℓP technolgy
- All plastic mold type
- Transparent lens
- Lineup: 6 colors (red, orange, yellow, pure yellow, green and pure green)
- High intensity light emission
- Excellent low current light output
- Applications: message boards, security devices and dashboard displays

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	4-3H1

Weight: 0.14 g

Lineup

Product Name	Color	Material
TLRE62T(F)	Red	InGaAℓP
TLRME62T(F)	Red	
TLSE62T(F)	Red	
TLOE62T(F)	Orange	
TLYE62T(F)	Yellow	
TLPYE62T(F)	Pure Yellow	
TLGE62T(F)	Green	
TLFGE62T(F)	Green	
TLPGE62T(F)	Pure Green	

Maximum Ratings (Ta = 25°C)

Product Name	Forward Current I_F (mA)	Reverse Voltage V_R (V)	Power Dissipation P_D (mW)	Operating Temperature T_{opr} (°C)	Storage Temperature T_{stg} (°C)
TLRE62T(F)	50	4	120	−40~100	−40~120
TLRME62T(F)	50	4	120		
TLSE62T(F)	50	4	120		
TLOE62T(F)	50	4	120		
TLYE62T(F)	50	4	120		
TLPYE62T(F)	50	4	120		
TLGE62T(F)	50	4	120		
TLFGE62T(F)	50	4	120		
TLPGE62T(F)	50	4	120		

Electrical and Optical Characteristics (Ta = 25°C)

Product Name	Typ. Emission Wavelength				Luminous Intensity I_V			Forward Voltage V_F			Reverse Current I_R	
	λ_d	λ_P	$\Delta\lambda$	I_F	Min	Typ.	I_F	Typ.	Max	I_F	Max	V_R
TLRE62T(F)	630	(644)	20	20	47.6	120	20	1.9	2.4	20	50	4
TLRME62T(F)	626	(636)	23	20	47.6	180	20	1.9	2.4	20	50	4
TLSE62T(F)	613	(623)	20	20	85	200	20	1.9	2.4	20	50	4
TLOE62T(F)	605	(612)	20	20	153	350	20	2.0	2.4	20	50	4
TLYE62T(F)	587	(590)	17	20	85	250	20	2.0	2.4	20	50	4
TLPYE62T(F)	580	(583)	14	20	47.6	150	20	2.0	2.4	20	50	4
TLGE62T(F)	571	(574)	17	20	47.6	110	20	2.0	2.4	20	50	4
TLFGE62T(F)	565	(568)	15	20	27.2	70	20	2.0	2.4	20	50	4
TLPGE62T(F)	558	(562)	14	20	15.3	45	20	2.1	2.4	20	50	4
Unit	nm			mA	mcd		mA	V		mA	μA	V

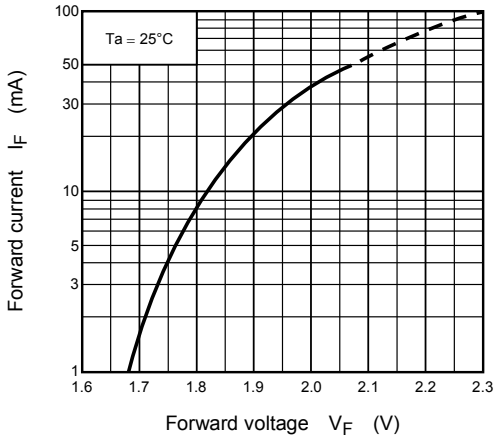
Precautions

Please be careful of the following:

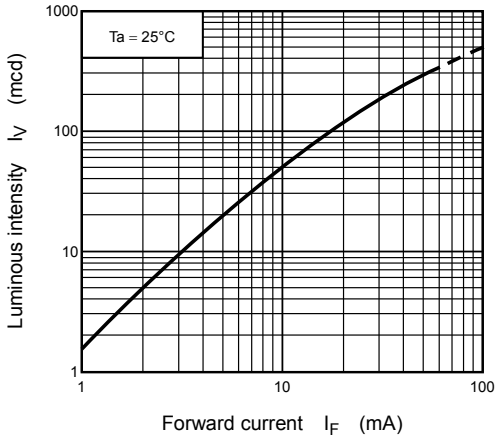
- Soldering temperature: 260°C max, soldering time: 3 s max
  (soldering portion of lead: up to 2 mm from the body of the device)
- If the lead is formed, the lead should be formed up to 5 mm from the body of the device without forming stress to the resin. Soldering should be performed after lead forming.
- This visible LED lamp also emits some IR light.
  If a photodetector is located near the LED lamp, please ensure that it will not be affected by this IR light.

TLRE62T(F)

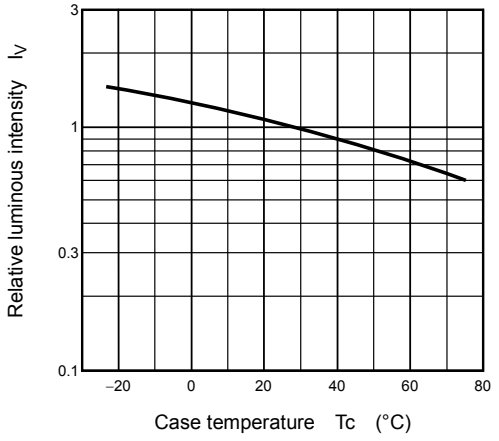
$I_F - V_F$



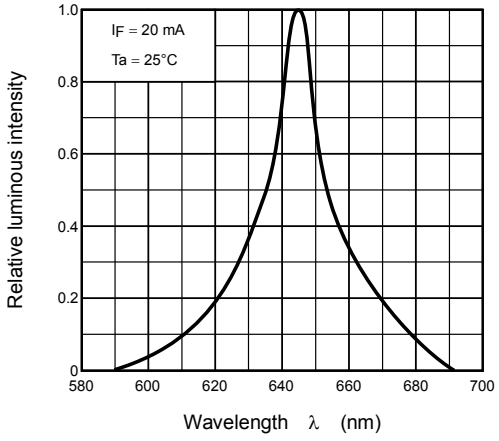
$I_V - I_F$



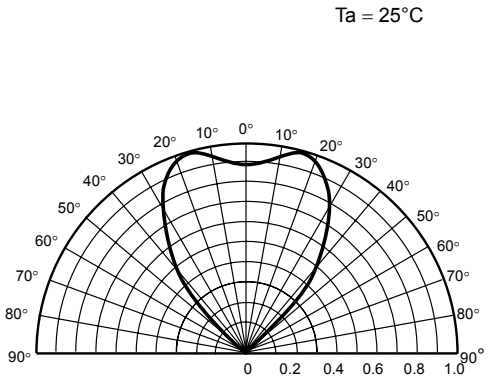
$I_V - Tc$



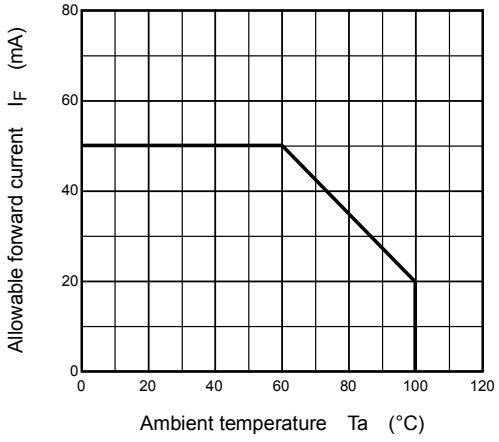
Relative luminous intensity – Wavelength



Radiation pattern

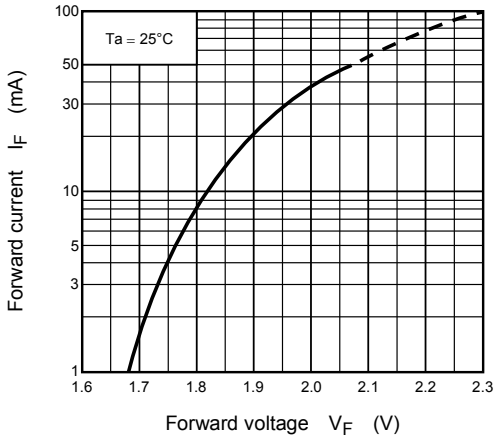


$I_F - Ta$

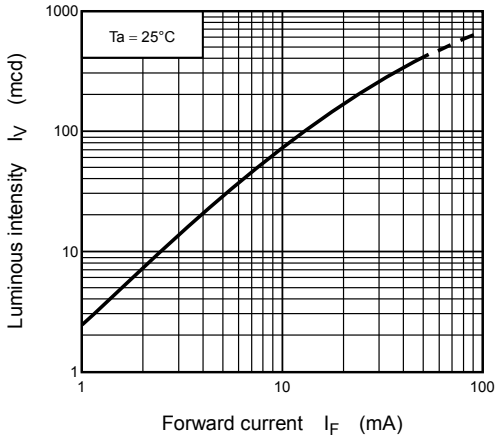


TLRME62T(F)

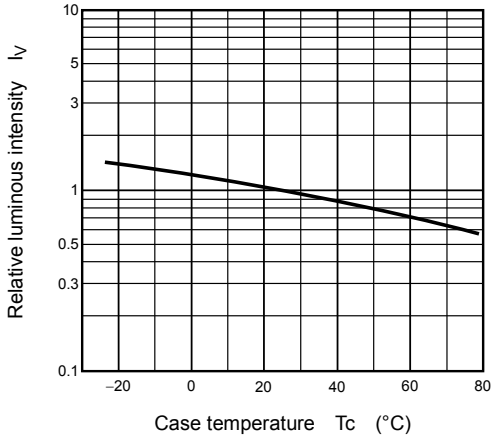
$I_F - V_F$



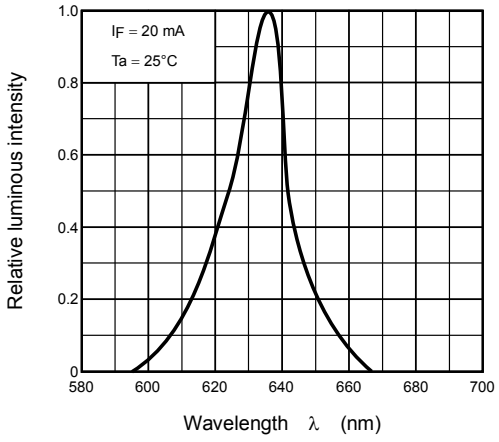
$I_V - I_F$



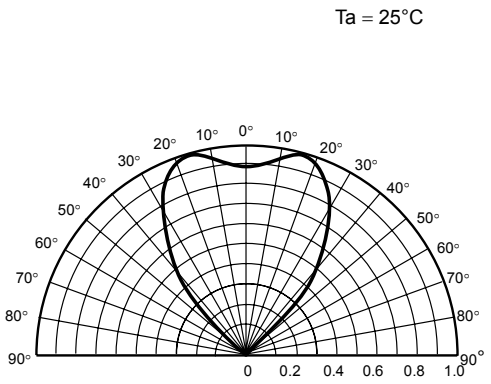
$I_V - Tc$



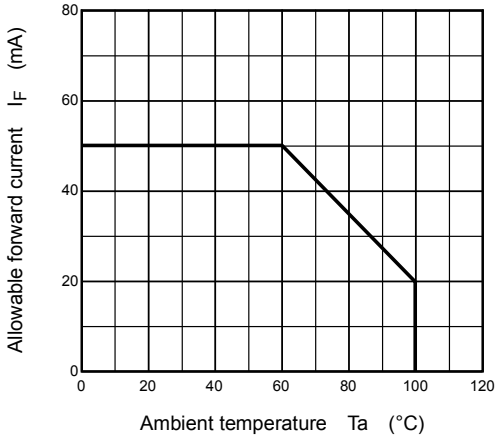
Relative luminous intensity – Wavelength



Radiation pattern

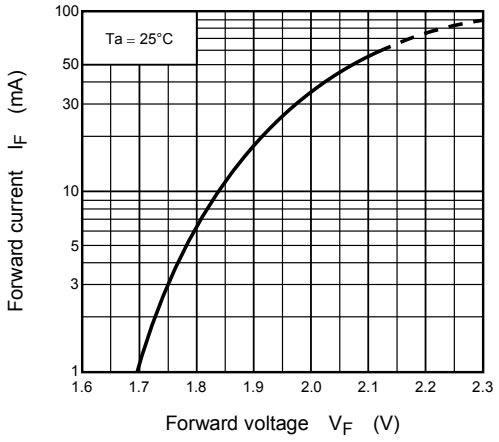


$I_F - Ta$

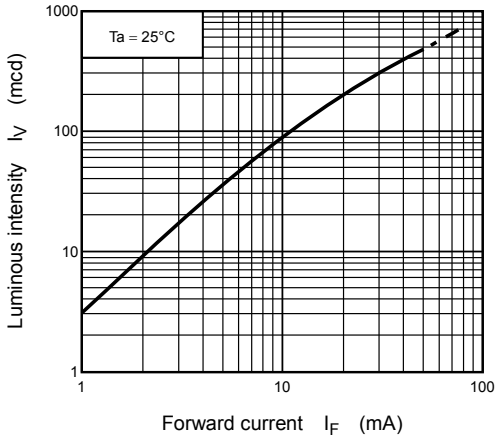


TLSE62T(F)

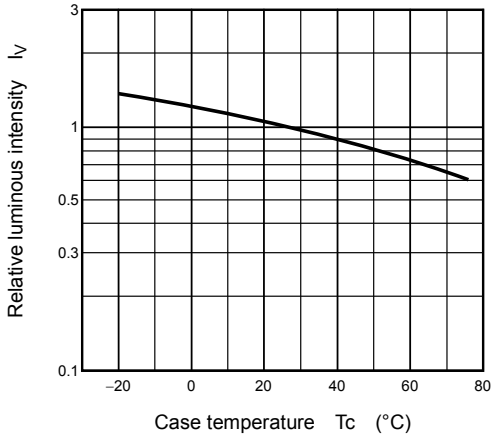
$I_F - V_F$



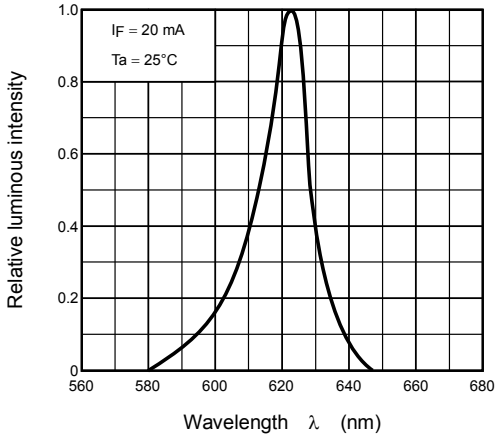
$I_V - I_F$



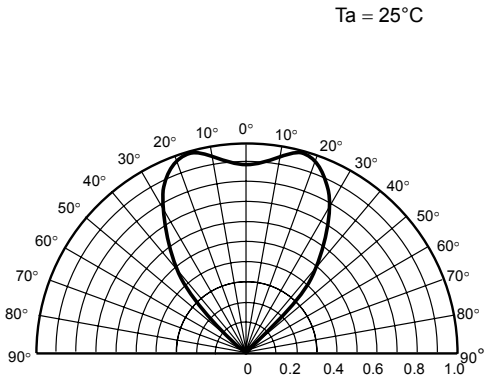
$I_V - Tc$



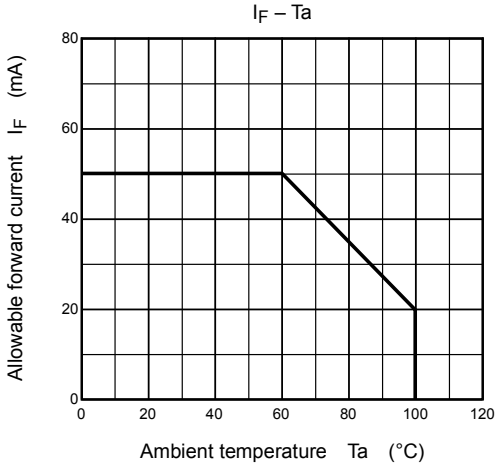
Relative luminous intensity – Wavelength



Radiation pattern

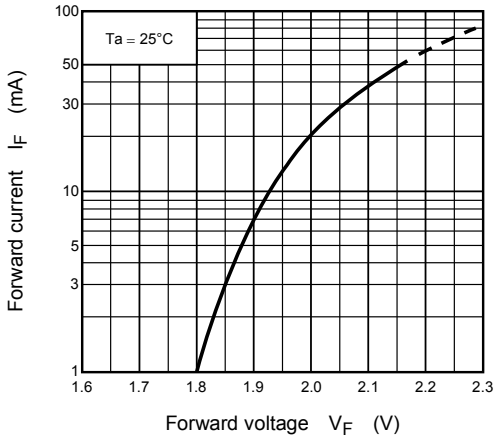


$I_F - Ta$

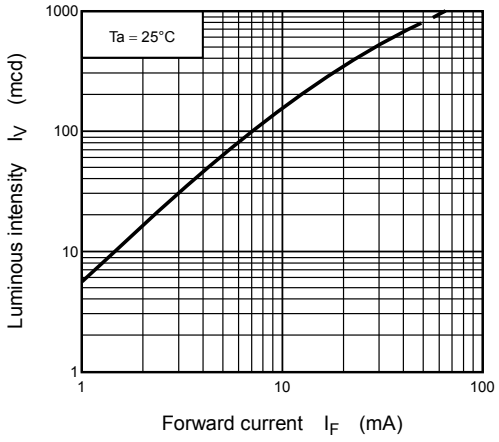


TLOE62T(F)

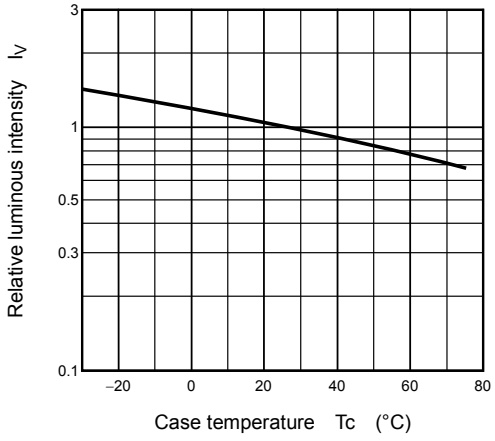
$I_F - V_F$



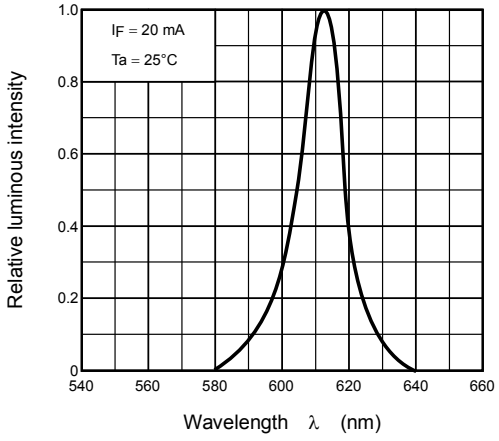
$I_V - I_F$



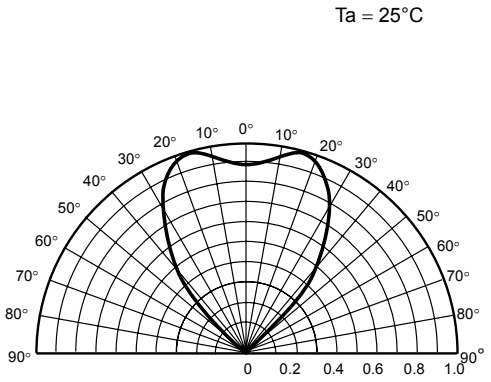
$I_V - Tc$



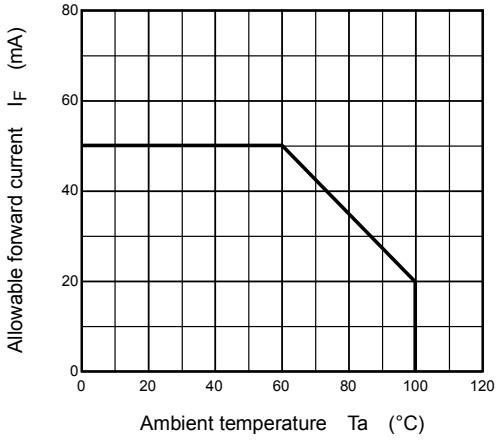
Relative luminous intensity – Wavelength



Radiation pattern

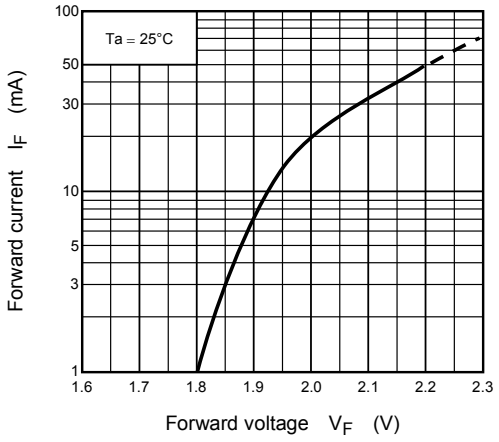


$I_F - Ta$

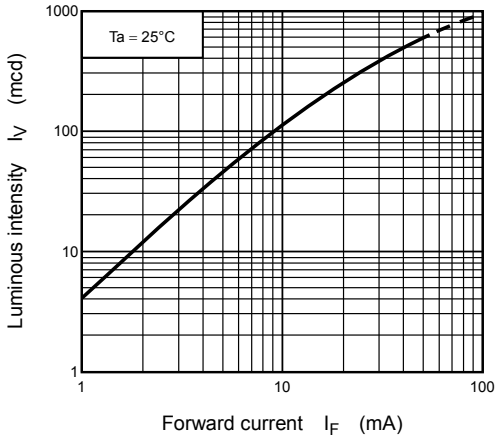


TLYE62T(F)

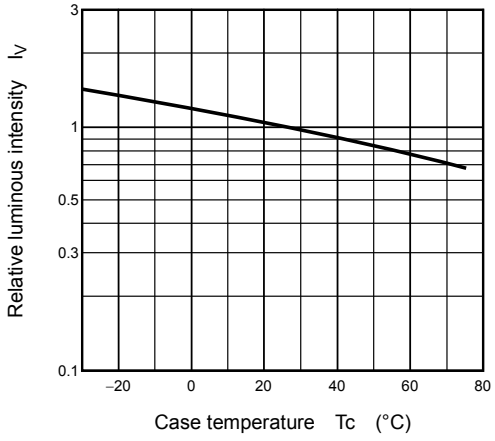
$I_F - V_F$



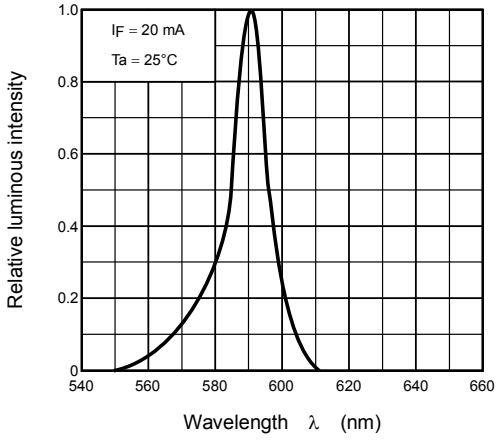
$I_V - I_F$



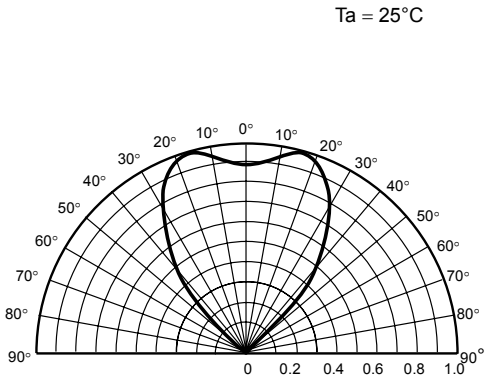
$I_V - Tc$



Relative luminous intensity – Wavelength



Radiation pattern



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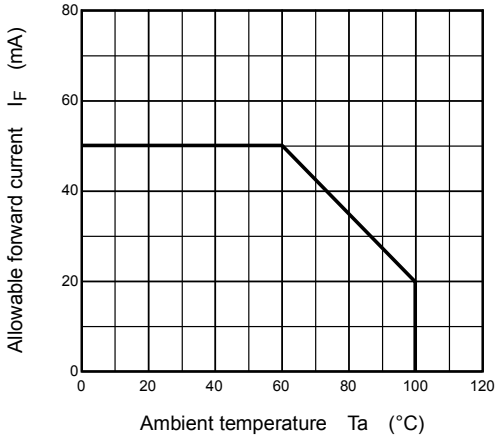
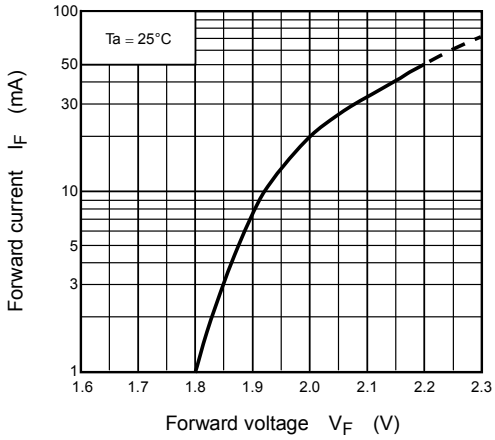
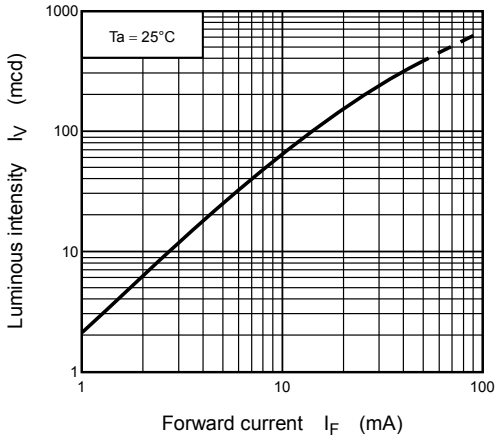


TLPYE62T(F)

$I_F - V_F$



$I_V - I_F$



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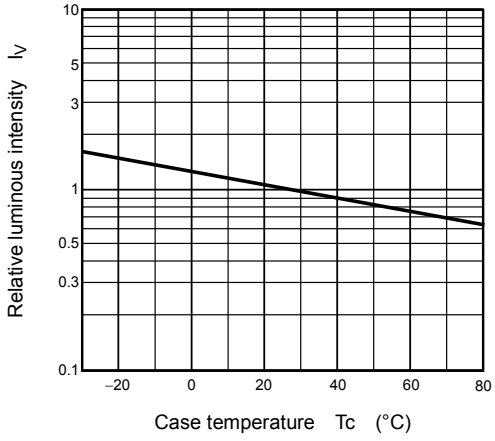
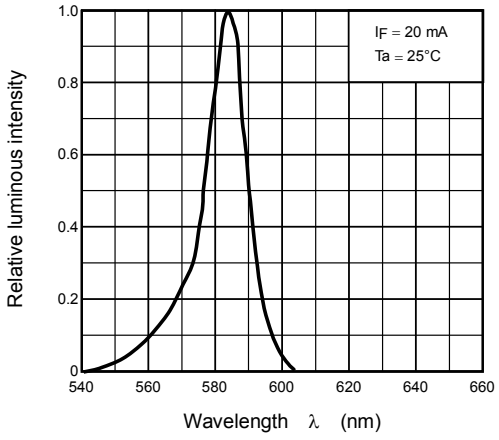
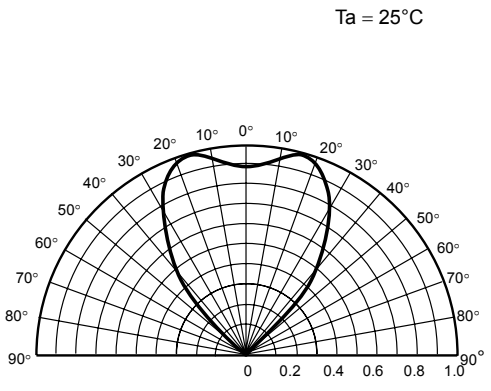


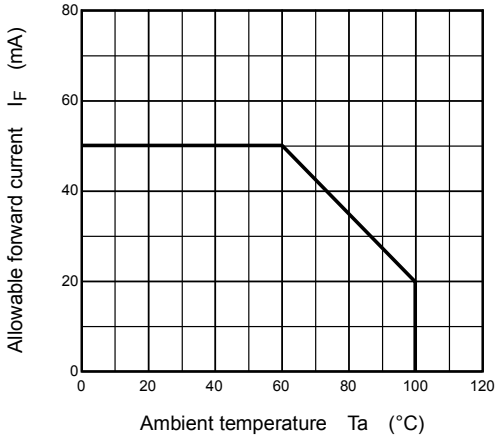
Relative luminous intensity – Wavelength



Radiation pattern

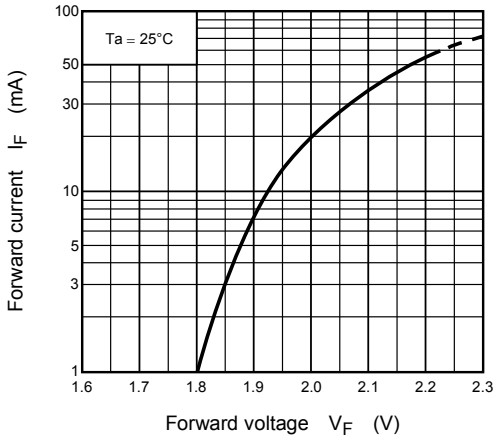


$I_F - Ta$

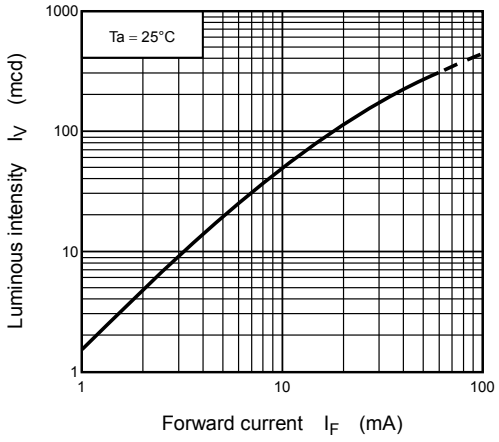


TLGE62T(F)

$I_F - V_F$



$I_V - I_F$



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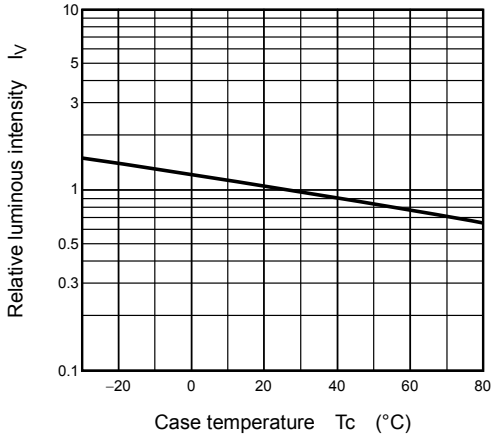
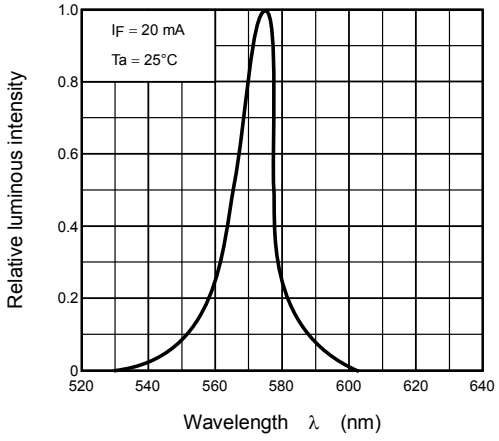
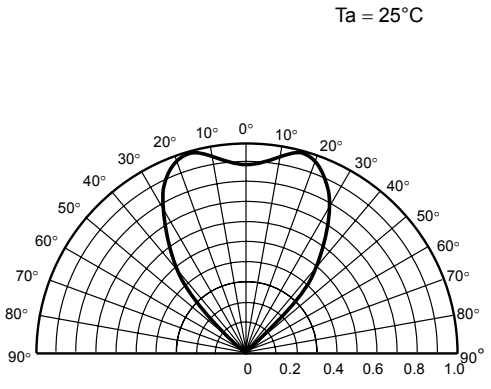


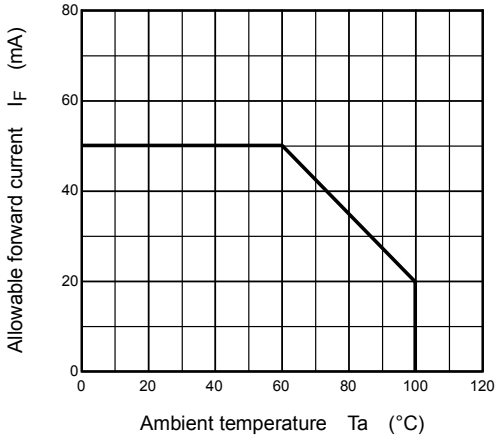
Relative luminous intensity – Wavelength



Radiation pattern

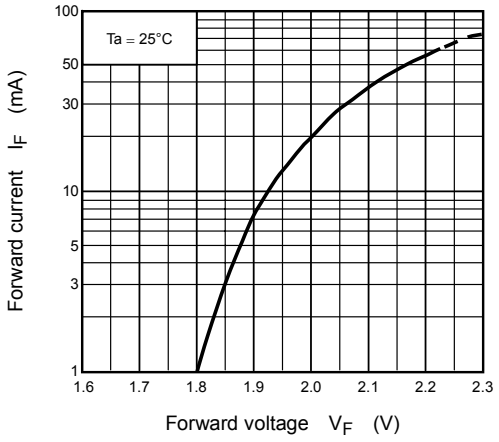


$I_F - Ta$

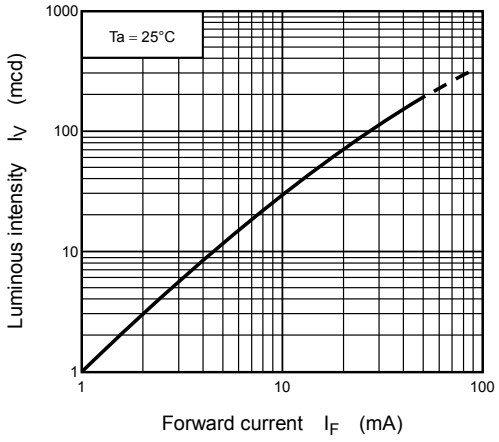


TLFGE62T(F)

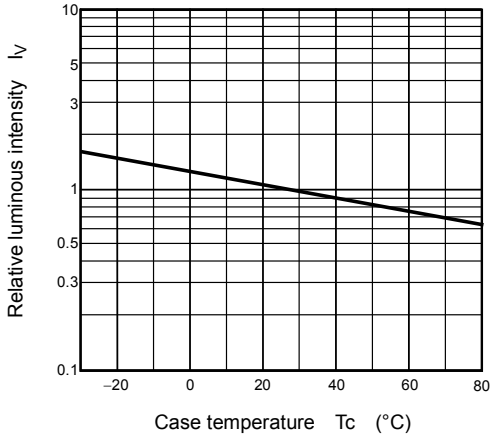
$I_F - V_F$



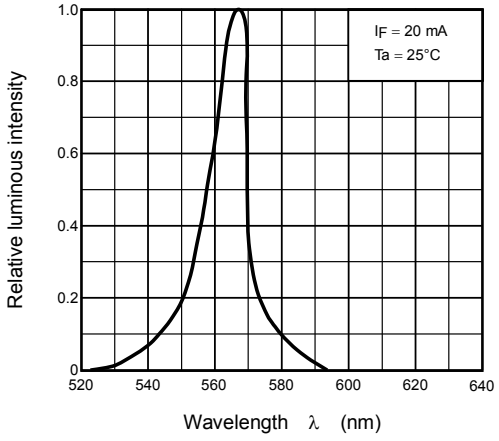
$I_V - I_F$



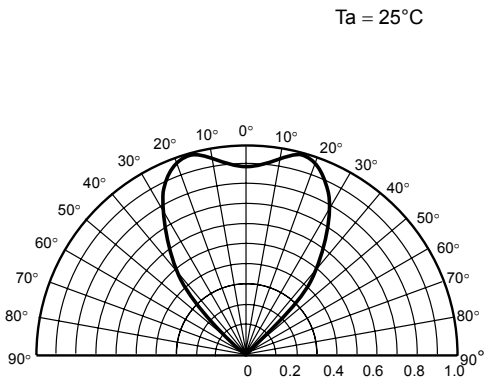
$I_V - Tc$



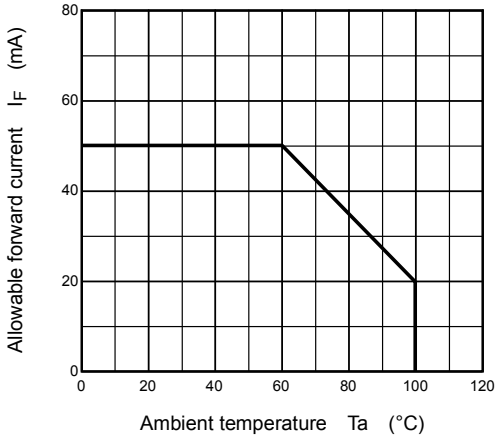
Relative luminous intensity – Wavelength



Radiation pattern

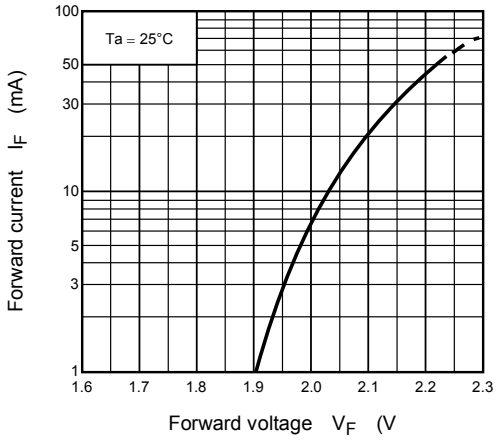


$I_F - Ta$

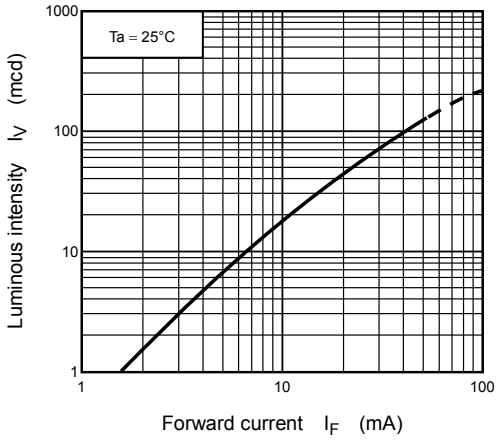


TLPGE62T(F)

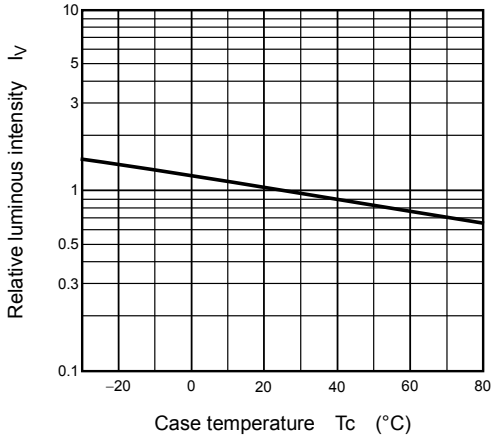
$I_F - V_F$



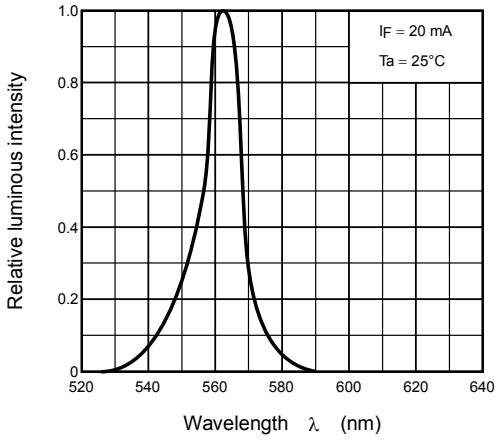
$I_V - I_F$



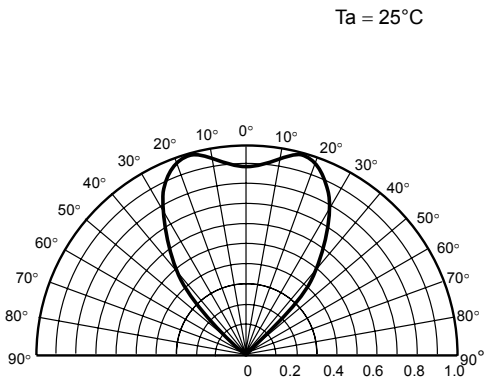
$I_V - Tc$



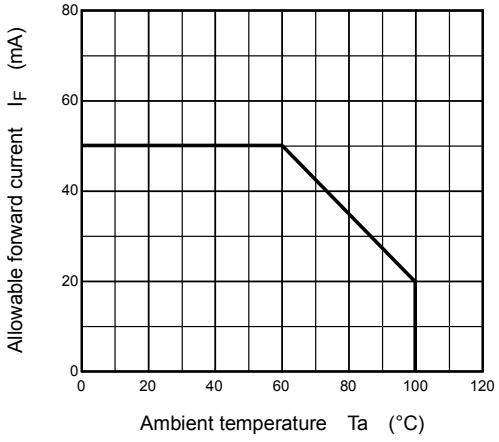
Relative luminous intensity – Wavelength



Radiation pattern



$I_F - Ta$



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